P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
- 100	0.075 at V_{GS} = - 10 V	- 9	22
	0.08 at V_{GS} = - 4.5 V	- 8	

FEATURES

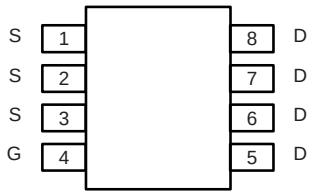
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

RoHS COMPLIANT

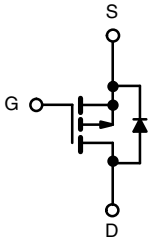
APPLICATIONS

- Networking
- LED Lighting Application
- Portable Equipment
- DC-DC Power Management

SO-8



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 9	A
	T_C = 70 °C		- 7.5	
Pulsed Drain Current		I_{DM}	- 36	
Avalanche Current		I_{AS}	- 8.8	
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	5.5[b]	W
	T_C = 70 °C		3.5	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	45	°C/W
Junction-to-Case (Drain)	R_{thJC}	3.8	

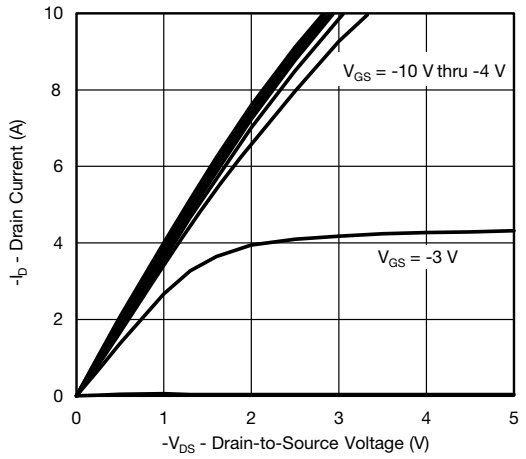
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{DS} = 0 V, I_D = - 250 µA	- 100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1		- 3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 100 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 80 V, V_{GS} = 0 V, T_J = 125 °C			- 50	
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 6 A		0.075	0.095	Ω
		V_{GS} = - 4.5 V, I_D = - 5 A		0.08	0.110	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 20 V, I_D = - 6 A		15.5		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 50 V, f = 1 MHz		3720		pF
Output Capacitance	C_{oss}			104		
Reverse Transfer Capacitance	C_{rss}			43		
Total Gate Charge[c]	Q_g	V_{DS} = - 50 V, V_{GS} = - 10 V, I_D = - 6 A		53.5		nC
		V_{DS} = - 50 V, V_{GS} = - 4.5 V, I_D = - 5 A		22		
Gate-Source Charge[c]	Q_{gs}			14		
Gate-Drain Charge[c]	Q_{gd}			8.8		
Gate Resistance	R_g	f = 1 MHz		7.5		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 50 V, R_L = 17.2 Ω $I_D \cong$ - 6 A, V_{GEN} = - 10 V, R_g = 1 Ω		10		ns
Rise Time[c]	t_r			22		
Turn-Off Delay Time[c]	$t_{d(off)}$			85		
Fall Time[c]	t_f			50		
Drain-Source Body Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				- 9	A
Pulsed Current	I_{SM}				- 36	
Forward Voltage[a]	V_{SD}	I_F = - 2.9 A, V_{GS} = 0 V		- 0.7	- 1.3	V
Reverse Recovery Time	t_{rr}	I_F = - 2.9 A, dI/dt = 100 A/µs		26		ns
Reverse Recovery Charge	Q_{rr}			38		nC

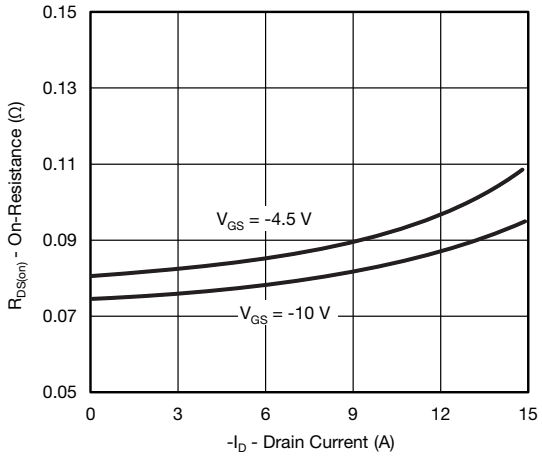
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

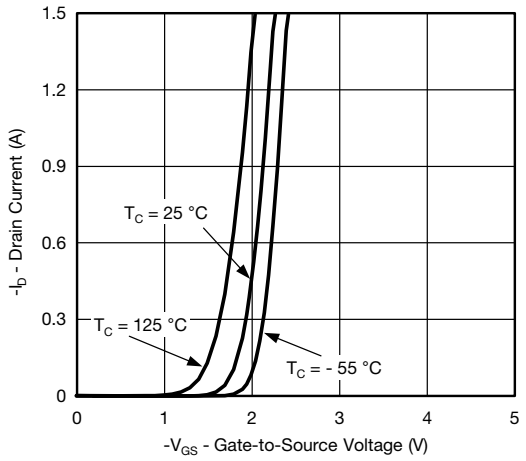
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



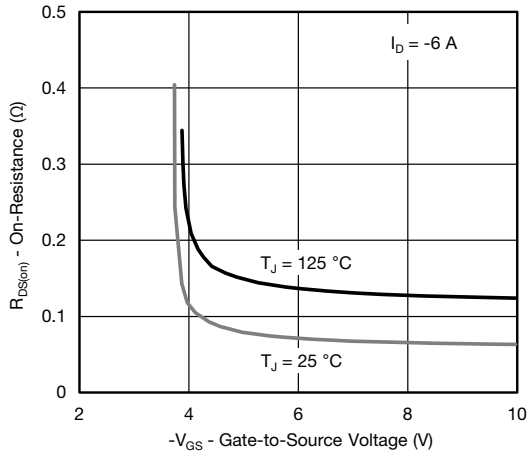
Output Characteristics



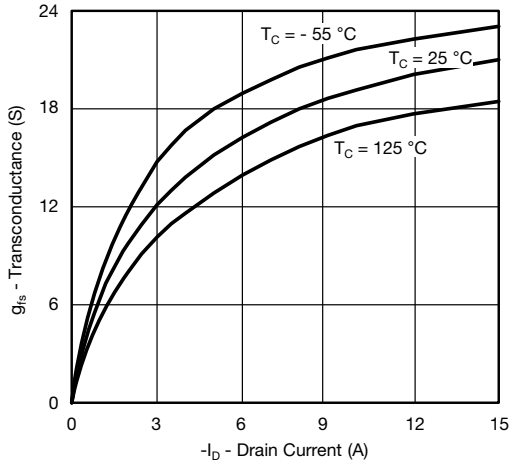
On-Resistance vs. Drain Current



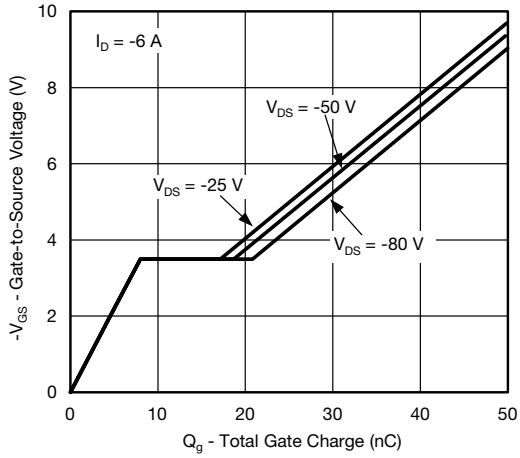
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

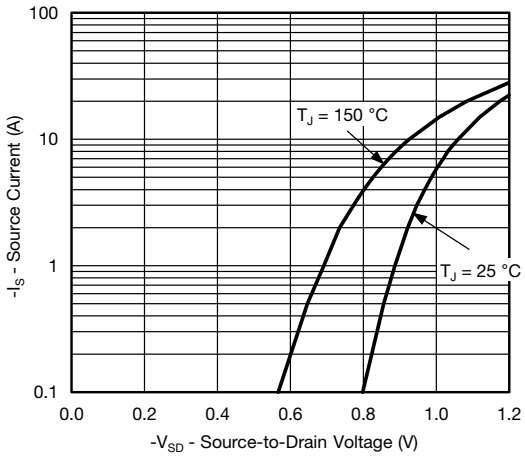


Transconductance

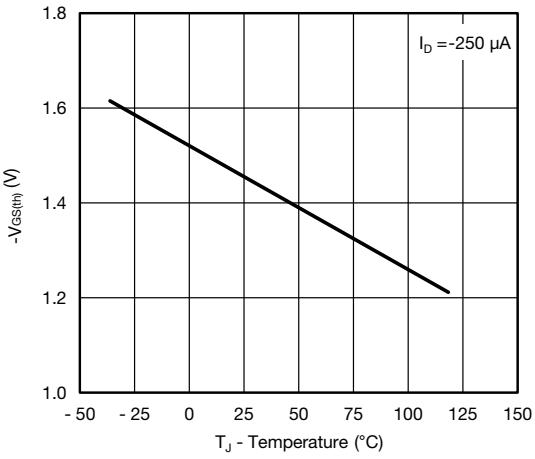


Gate Charge

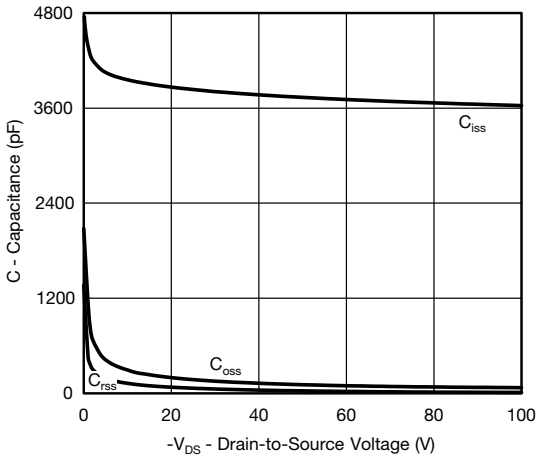
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



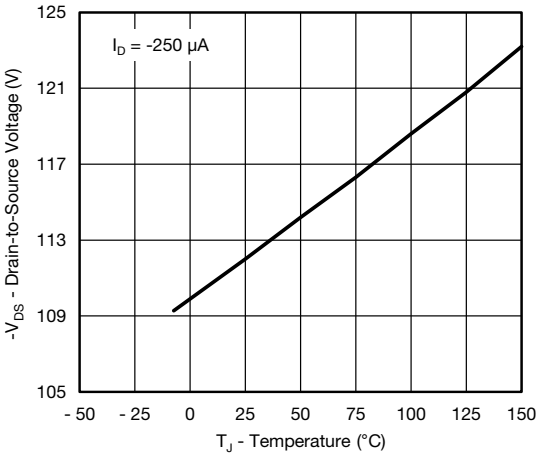
Source-Drain Diode Forward Voltage



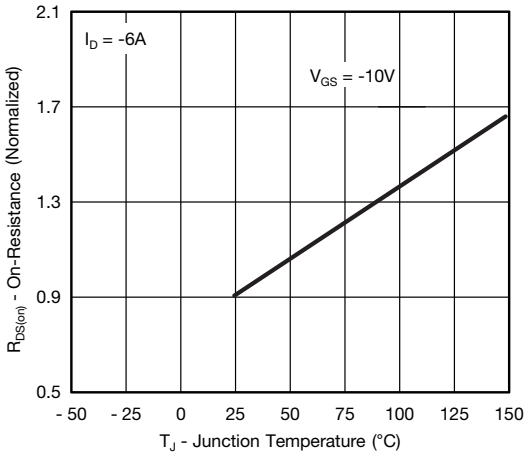
Threshold Voltage



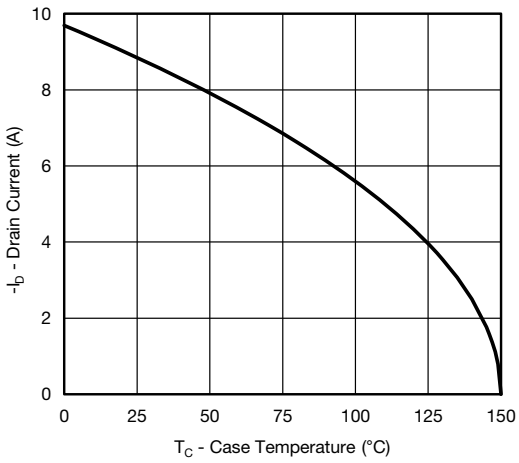
Capacitance



Drain Source Breakdown vs. Junction Temperature

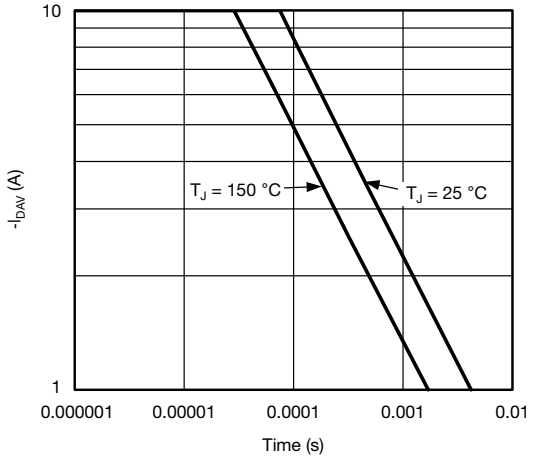


On-Resistance vs. Junction Temperature

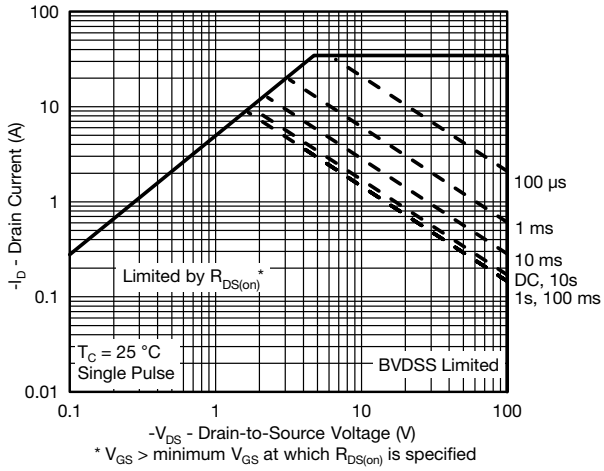


Current Derating

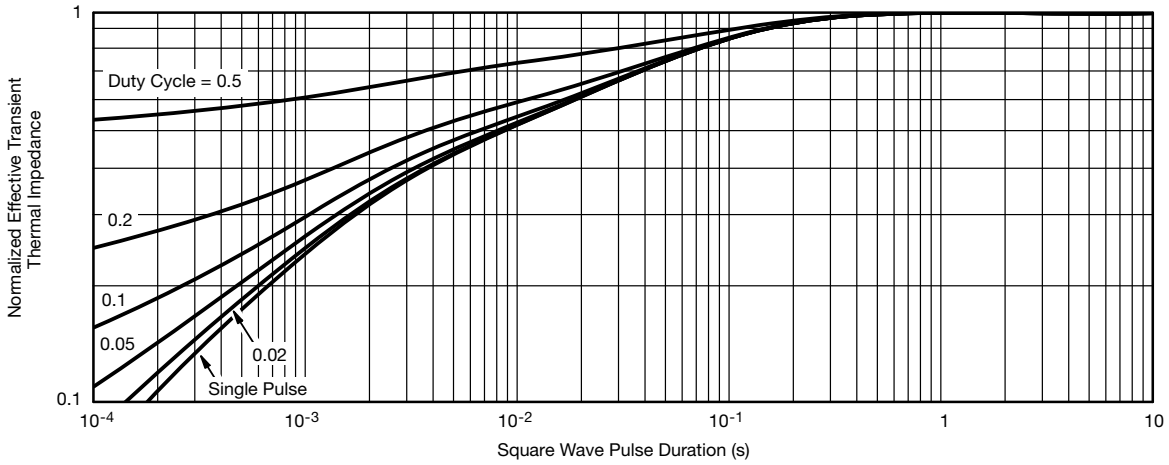
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time

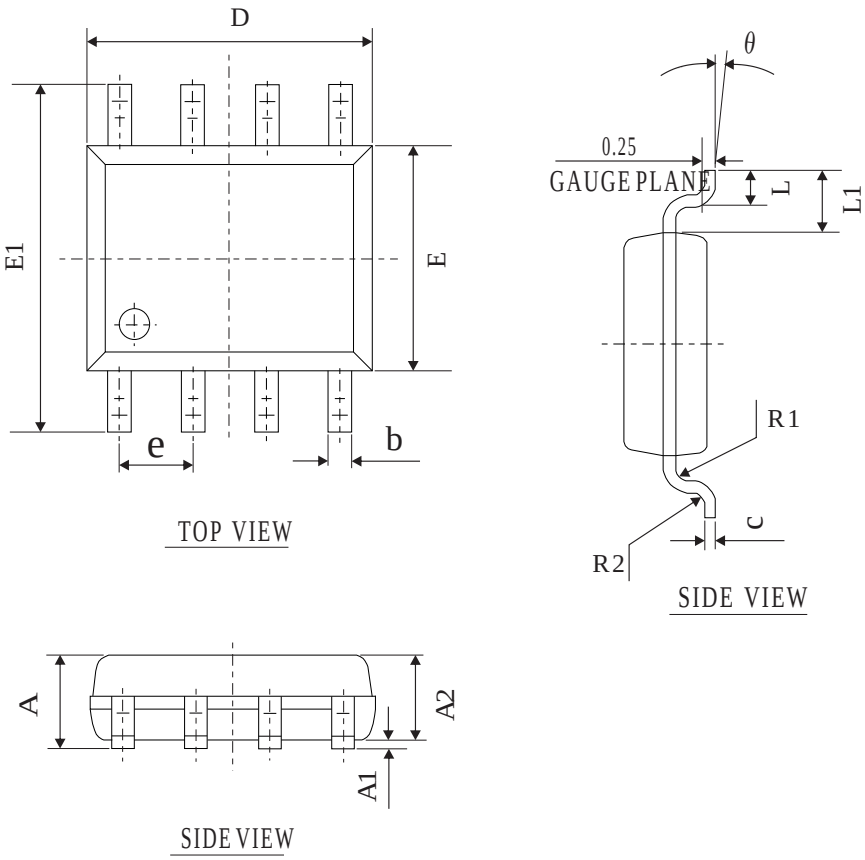


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

SOP-8 PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	1.30	1.60	1.85
A1	0.03	0.15	0.28
A2	1.20	1.45	1.70
b	0.26	0.40	0.54
C	0.132	0.203	0.273
D	4.50	4.90	5.30
E	3.50	3.00	4.30
E1	5.50	6.00	6.50
L	0.30	0.70	1.10
θ	2°	4°	6°
L1	1.04REF		
e	1.27BSC		
R1	0.07TYP		
R2	0.07TYP		

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